80V N-Channel Power SpeedFET

• General Description

It combines advanced trench MOSFET technology wit h a low resistance package to provide extremely low $R_{DS(ON)}$. It is suitable for automotive application.

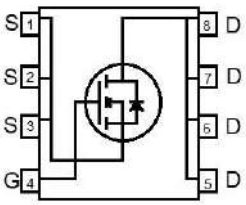
• Features

- AEC-Q101 Qualified
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

- BLDC Motor driver
- DC-DC
- Load Switch

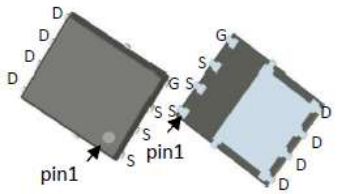
• Product Summary



V_{DS}= 80V

$R_{DS(ON)}$ = 1.9mΩ

I_D= 176A



DFN5*6

RoHS

REACH COMPLIANT

HF

• Ordering Information:

Part NO.	KPRZMS019N08H-V
Marking	ZMS019N08H

• Absolute Maximum Ratings (T_C=25℃)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		80	V
Gate-Source Voltage①	V_{GS}		±20	V
Continuous Drain Current	I_D	T_C=25℃	176	A
	I_D	T_C=75℃	144	A
	I_D	T_C=100℃	120	A
Pulsed Drain Current	I_{DM}	Pulsed; t_p ≤ 10 μs; T_{mb} = 25 ℃;	704	A
Total Power Dissipation	P_D	T_C=25℃	150	W
Total Power Dissipation	P_D	T_A=25℃	3.3	W
Operating Junction Temperature	T_J		-55 to +175	℃
Storage Temperature	T_{STG}		-55 to +175	℃
Single Pulse Avalanche Energy	E_{AS}	L=0.1mH, V_{GS}=10V, Rg=25Ω,	423	mJ
		L=0.5mH, V_{GS}=10V, Rg=25Ω,	698	mJ
ESD Level (HBM)	CLASS 2			

- **Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	1.0	°C/W
Thermal resistance, junction-ambient	R_{thJA}②		-	45	°C/W
Soldering temperature	Tsold		-	260	°C

- **Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V, I_D =250uA	80			V
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} =V_{DS}, I_D =250uA	2.0	2.7	4.0	V
Drain-Source Leakage Current	I_{DSS}	V_{GS}=0V, V_{DS}= 80V			1.0	uA
Gate- Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS} = 0V			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D= 30A		1.9	2.3	mΩ
Forward Transconductance	g_{FS}	V_{DS} =5V, I_{SD} = 10A		34		S
Diode Forward Voltage	V_{FSD}	V_{GS} =0V, I_{SD} = 30A			1.3	V

- **Dynamic characteristics**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	Ciss	V_{GS}=0V,V_{DS}=40V,f = 1MHz,	-	5431	-	pF
Output capacitance	Coss		-	1532	-	
Reverse transfer capacitance	Crss		-	49	-	
Gate Risistance	Rg	f = 1MHz	-	1.5		Ω
Total gate charge	Qg	V_{DD} = 15V, I_D = 30A, V_{GS} = 10V	-	91	-	nC
Gate - Source charge	Qgs		-	23	-	
Gate - Drain charge	Qgd		-	24	-	
Turn-ON Delay time	$t_{D(on)}$	V_{GS}=10V,V_{DS}=15V, R_G =3.3Ω, I_D =20A	-	17	-	ns
Turn-ON Rise time	t_r		-	12	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	30	-	ns
Turn-Off Fall time	t_f		-	21	-	ns
Reverse Recovery Time	t_{RR}	V_{DD}=20V, dI_S/dt = 100A/us, I_S=50A	-	87	-	ns
Reverse Recovery Charge	Q_{RR}		-	142	-	nC

Fig.1 Gate-Charge Characteristics

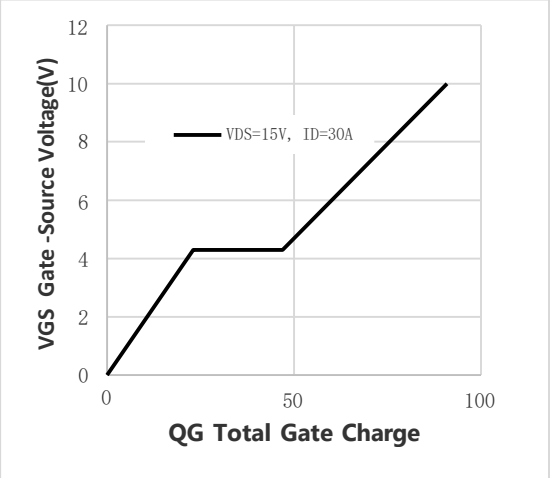


Fig.2 Capacitance Characteristics

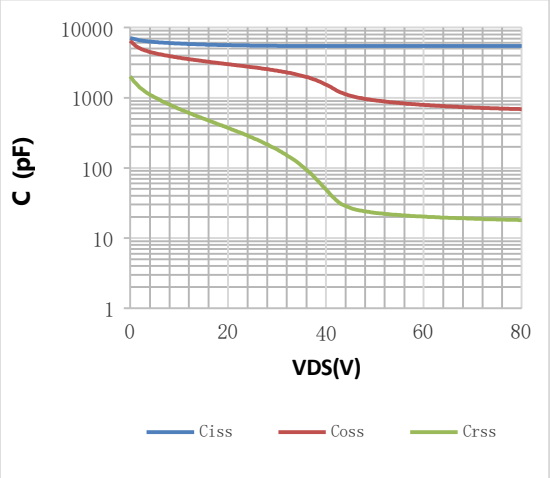


Fig.3 Power Dissipation

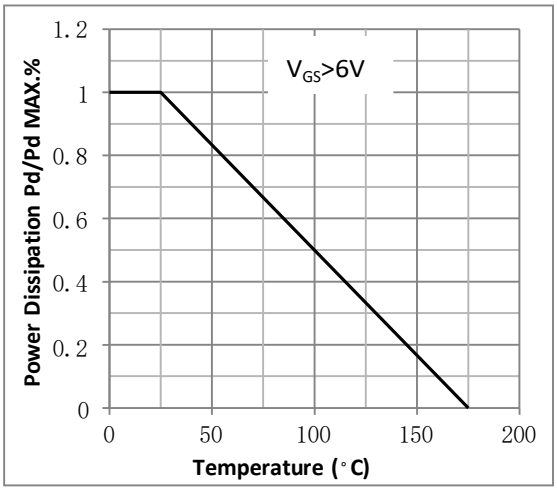


Fig.4 Typical output Characteristics

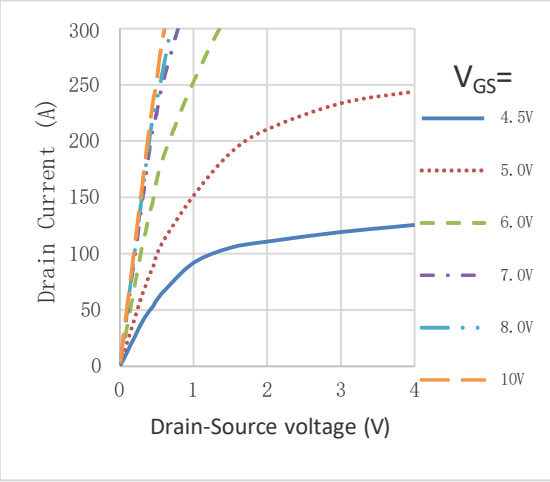


Fig.5 Threshold Voltage V.S Junction Temperature

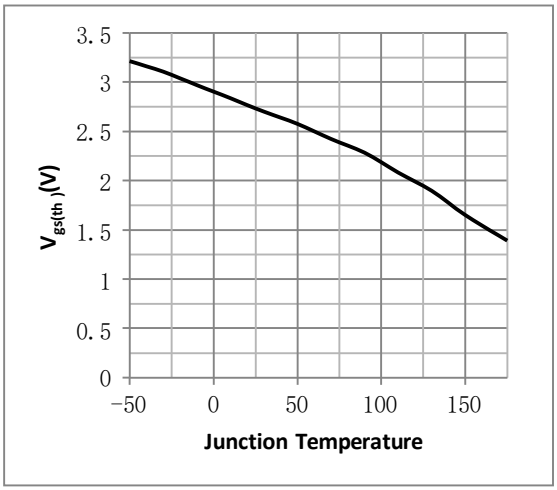


Fig.6 Resistance V.S Drain Current

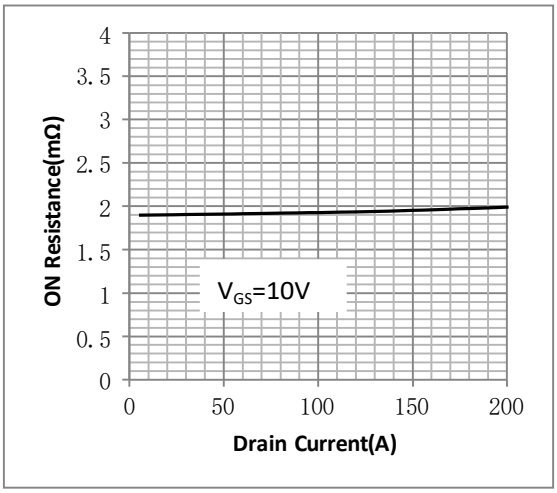


Fig.7 On-Resistance VS Gate Source Voltage

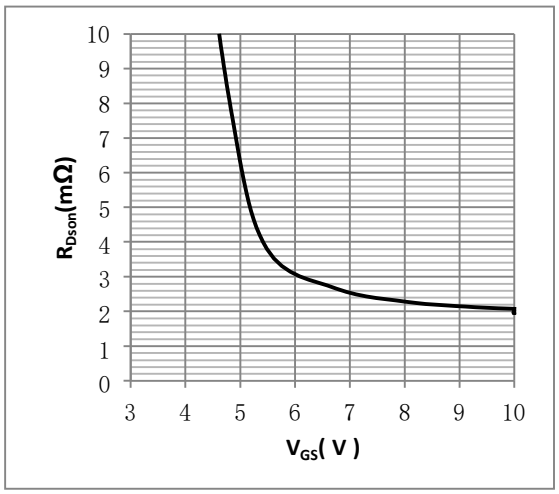


Fig.8 On-Resistance V.S Junction Temperature

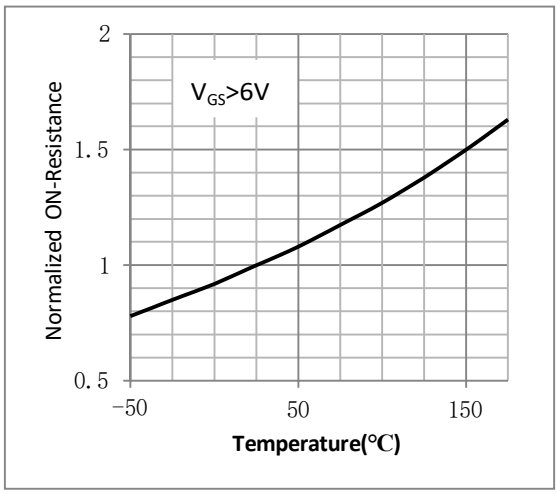


Figure 9. Diode Forward Voltage vs. Current

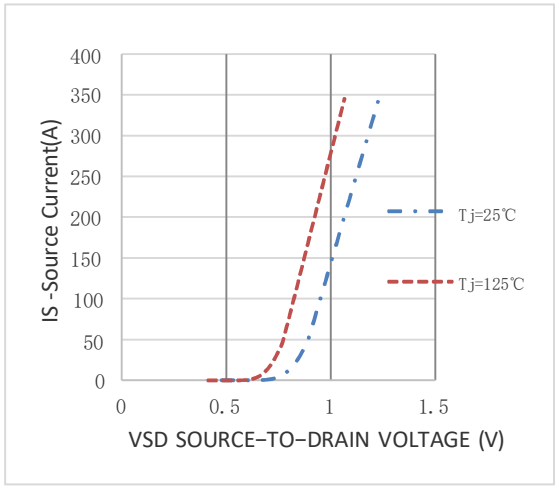


Figure 10. Transfer Characteristics

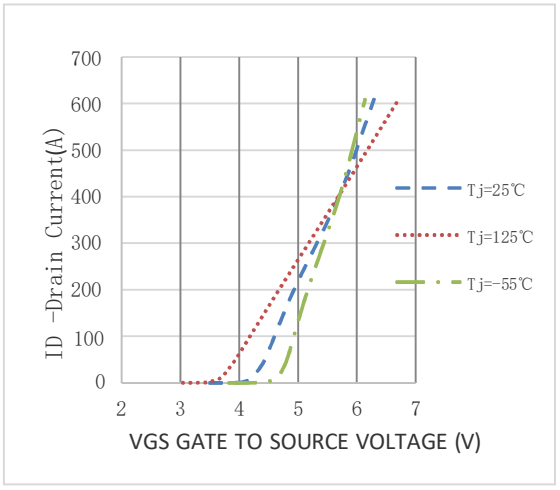


Fig.11 Safe Operating Area

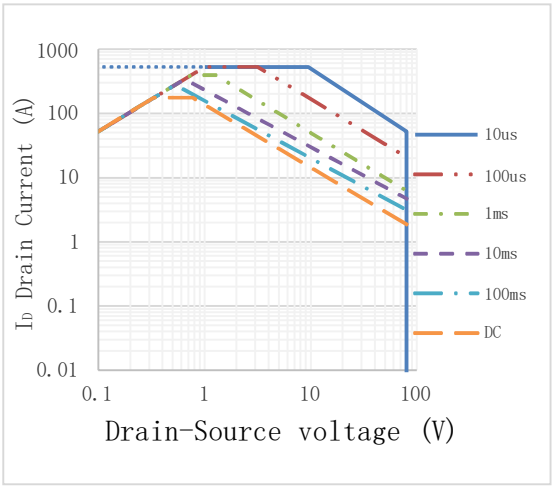
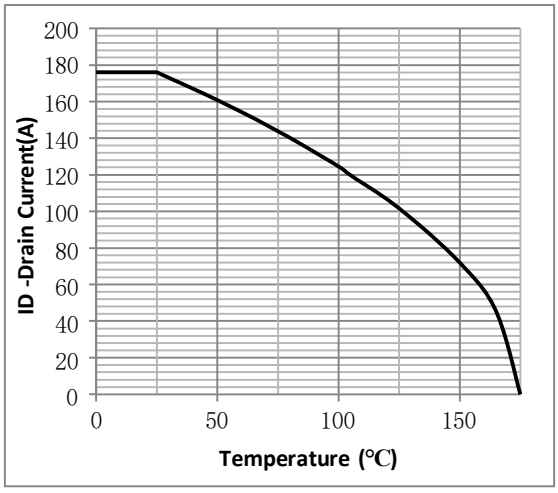
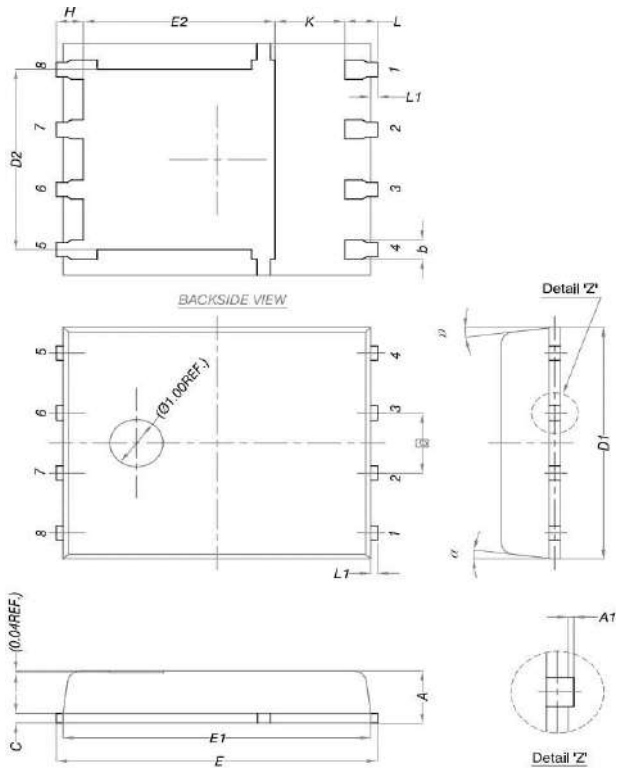


Fig.12 ID vs. Junction Temperature③



- **DFN5*6 Package Outline**



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°